

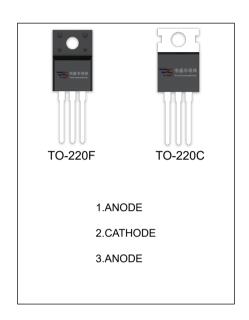
# SBD20150LCTB、SBDF20150LCTB SCHOTTKY BARRIER RECTIFIER

### MAIN CHARACTERISTICS

Io	20 (2×10) A				
$V_{RRM}$	150 V				
T <sub>j</sub>	150 ℃				
$V_{F(typ)}$	0.64V (@Tj=125℃)				

### **FEATURES**

- Low Power Loss, High Efficiency
- Guard Ring Die Construction for Transient Protection
- High Current Capability and Low Forward Voltage Drop



# MAXIMUM RATINGS ( T<sub>a</sub>=25°C unless otherwise noted )

Symbol	Parameter	SBD		Unit
Symbol	Symbol		20150LCTB F20150LCTB	
$V_{RRM}$	Peak repetitive reverse voltage			
V <sub>RWM</sub>	Working peak reverse voltage	150		V
V <sub>R</sub>	DC blocking voltage			
V <sub>R(RMS)</sub>	RMS reverse voltage	105		V
lo	Average rectified output current	20		Α
I <sub>FSM</sub>	Non-Repetitive peak forward surge current (8.3ms half sine wave)	150		Α
R <sub>ΘJc</sub>	Thermal resistance from junction to case ,Tc=25℃	2.0	3.0	°C/W
R <sub>OJA</sub>	Thermal resistance from junction to ambient	62.5		°C/W
Tj	Junction temperature	150		°C
T <sub>stg</sub>	Storage temperature	-55~+150		$^{\circ}$

# **ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25℃ unless otherwise specified)**

Parameter	Symbol	Test conditions		Min	Тур	Max	Unit
Reverse voltage	V <sub>(BR)</sub>	I <sub>R</sub> =1mA		150			V
Reverse current	I <sub>R</sub>	V <sub>R</sub> =150V	Tj =25℃		5.0	100	uA
			Tj =125℃		5.0		mA
Forward voltage	V <sub>F</sub>	I <sub>F</sub> =5A	Tj =25℃		0.72		٧
			Tj =125℃		0.57		V
		I <sub>F</sub> =10A	Tj =25℃		0.78	0.85	V
			Tj =125℃		0.64		V

<sup>\*</sup>Pulse test: pulse width ≤300µs, duty cycle≤ 2.0%.



